Switch-mode Power Rectifiers

DPAK-3 Surface Mount Package

MBRD620CT, NRVBD620VCT, SBRV620CT Series

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

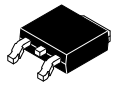
Features

- Extremely Fast Switching
- Extremely Low Forward Drop
- Platinum Barrier with Avalanche Guardrings
- NRVBD and SBRV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

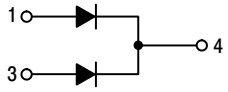
Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260 °C Max. for 10 Seconds
- ESD Ratings:
  - Machine Model = C
  - Human Body Model = 3B

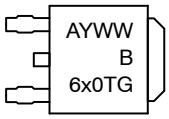
SCHOTTKY BARRIER RECTIFIERS
6.0 AMPERES, 20 – 60 VOLTS



DPAK3
CASE 369C



MARKING DIAGRAM



A	= Assembly Location*
Y	= Year
WW	= Work Week
B6x0T	= Device Code
x	= 2, 3, 4, 5, or 6
G	= Pb-Free Package

* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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MAXIMUM RATINGS

Rating	Symbol	MBRD/NRVBD/SBRV					Unit
		620CT	630CT	640CT	650CT	660CT	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	50	60	V
Average Rectified Forward Current T_C = 130 °C Per Diode Per Device	$I_{F(AV)}$			3 6			A
Peak Repetitive Forward Current, T_C = 130 °C (Square Wave, Duty = 0.5) Per Diode	I_{FRM}			6			A
Nonrepetitive Peak Surge Current – (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}			75			A
Peak Repetitive Reverse Surge Current (2 μs, 1 kHz)	I_{RRM}			1			A
Operating Junction Temperature (Note 1)	T_J			−65 to +175			°C
Storage Temperature	T_{stg}			−65 to +175			°C
Voltage Rate of Change (Rated V_R)	dv/dt			10,000			V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6	°C/W
Maximum Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	°C/W

2. Rating applies when surface mounted on the minimum pad size recommended.

ELECTRICAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) i_F = 3 Amps, T_C = 25 °C i_F = 3 Amps, T_C = 125 °C i_F = 6 Amps, T_C = 25 °C i_F = 6 Amps, T_C = 125 °C	V_F	 0.7 0.65 0.9 0.85	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T_C = 25 °C) (Rated dc Voltage, T_C = 125 °C)	i_R	 0.1 15	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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TYPICAL CHARACTERISTICS

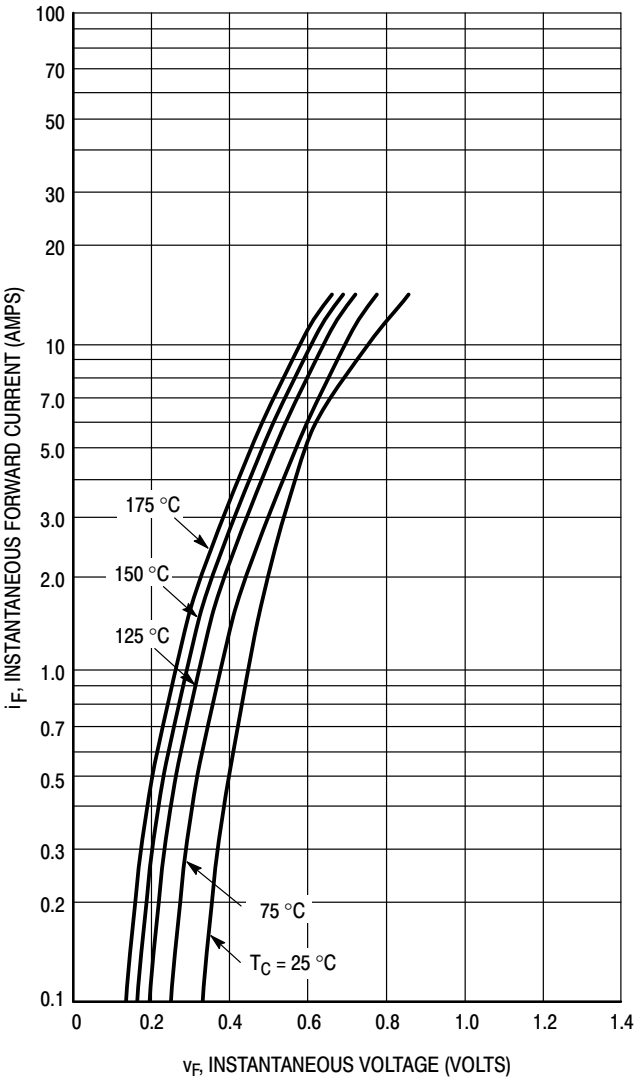
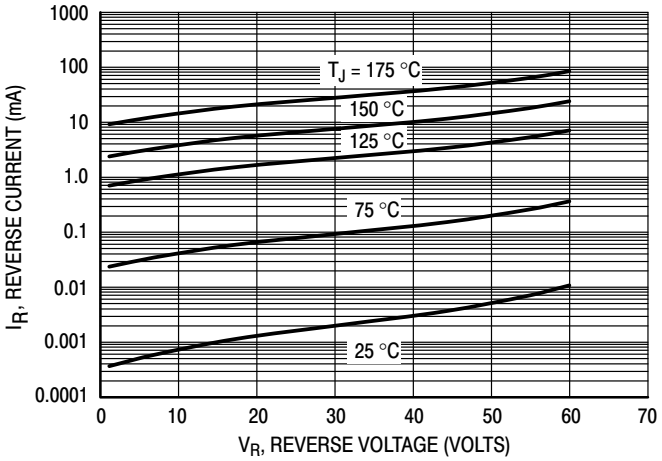


Figure 1. Typical Forward Voltage, Per Leg



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R.

Figure 2. Typical Reverse Current,* Per Leg

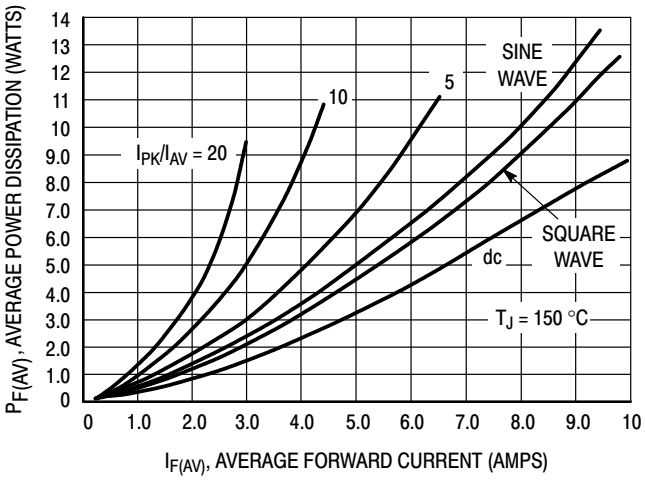


Figure 3. Average Power Dissipation, Per Leg

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TYPICAL CHARACTERISTICS

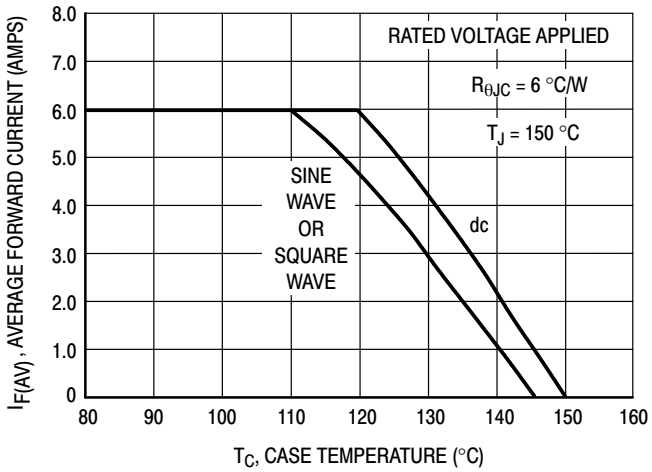


Figure 4. Current Derating, Case, Per Leg

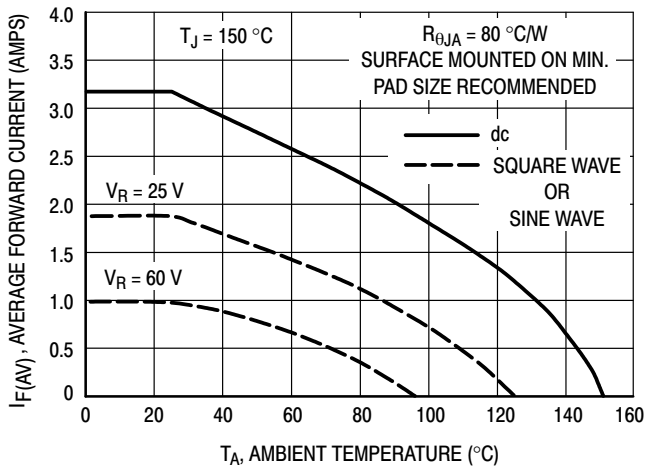


Figure 5. Current Derating, Ambient, Per Leg

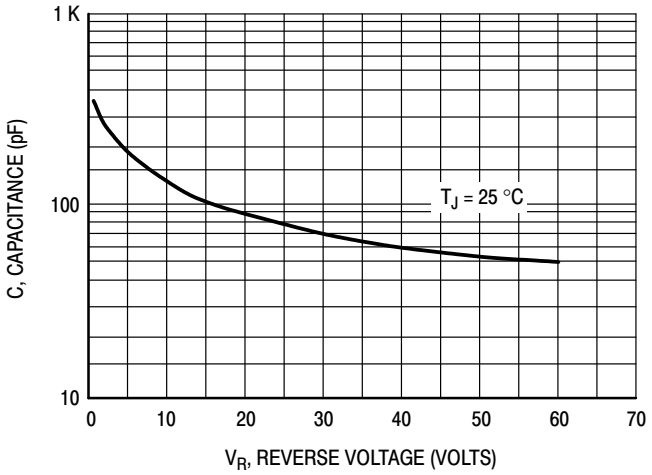


Figure 6. Typical Capacitance, Per Leg

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ORDERING INFORMATION

Device	Package	Shipping†
MBRD620CTT4G	DPAK3 (Pb-Free)	2500 / Tape & Reel
MBRD640CTT4G		2500 / Tape & Reel
MBRD650CTT4G		2500 / Tape & Reel
MBRD660CTT4G		2500 / Tape & Reel
SBRV660VCTT4G*		2500 / Tape & Reel
SNRVBD660CTT4G*		2500 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

* NRVBD and SBRV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

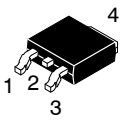
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REVISION HISTORY

Revision	Description of Changes	Date
17	Removed EOL (discontinued) devices.	10/6/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

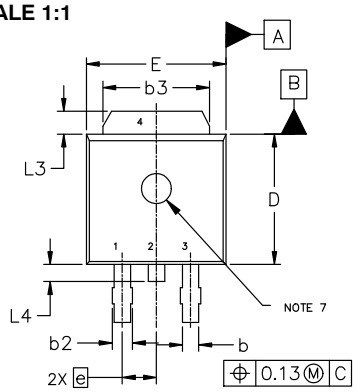
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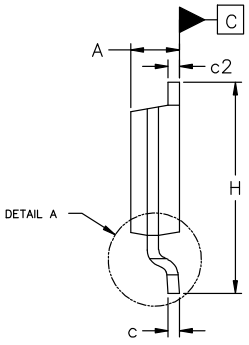
SCALE 1:1

DPAK3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE J

DATE 12 AUG 2025

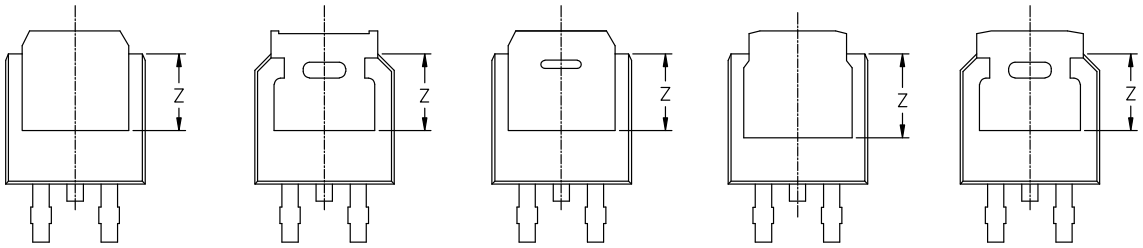


TOP VIEW



SIDE VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	2.18	2.28	2.38
A1	0.00	---	0.13
b	0.63	0.76	0.89
b2	0.72	0.93	1.14
b3	4.57	5.02	5.46
c	0.46	0.54	0.61
c2	0.46	0.54	0.61
D	5.97	6.10	6.22
E	6.35	6.54	6.73
e	2.29 BSC		
H	9.40	9.91	10.41
L	1.40	1.59	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	---	1.27
L4	---	---	1.01
Z	3.93	---	---

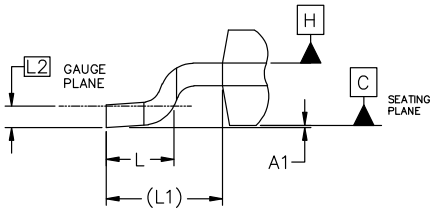


BOTTOM VIEW

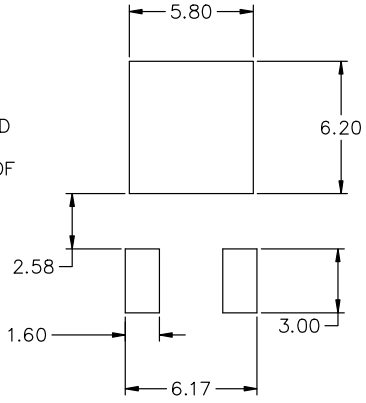
ALTERNATE CONSTRUCTIONS

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15mm PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.



DETAIL A
ROTATED 90° CW



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB–FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

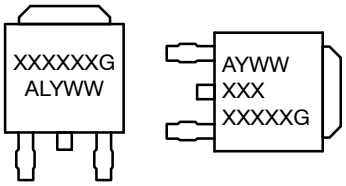
DOCUMENT NUMBER:	**98AON10527D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**DPAK3 6.10x6.54x2.28, 2.29P**	**PAGE 1 OF 2**

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DPAK3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE J

DATE 12 AUG 2025

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX	= Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

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